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N-Channel 150 V (D-S) Super Junction MOSFET

Features

· DT-SJ Power MOSFET

· Low Gate Charge

- 100 % Rg and UIS Tested
- · Pb-free Lead Plating

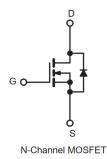
· Halogen-free and RoHS-compliant

$\mathbf{Q}_{\mathbf{g}}$ (Typ.) V_{DS} (V) $R_{DS(on)}$ (m Ω)(Typ.) $I_D(A)^a$ 5.2 at $V_{GS} = 10 \text{ V}$ 150 157 43 nC

PRODUCT SUMMARY

Applications

- Power Managerment in Telecom., Industrial Automation, CE
- Current Switching in DC/DC & AC/DC (SR) Sub-systems
- · Motor Driving in Power Tool, E-vehicle, Robotics



TO-247 Pin Configuration



ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)								
Parameter	Symbol	Limit	Unit					
Drain-Source Voltage			150	V				
Gate-Source Voltage	V _{GS}	± 20						
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	l _D	157					
	T _C = 100 °C	ן טי [99	Α				
Pulsed Drain Current		I _{DM}	489					
Single-Pulse Avalanche Energy		E _{AS}	540	mJ				
	T _C = 25 °C		347	W				
Maximum Power Dissipation	T _C = 100 °C	P _D	139					
	T _A = 25 °C	ם י	2.6 ^{b,c}					
	T _A = 100 °C		1.04 ^{b,c}					
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C				

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^b	t ≤ 10 s	R _{thJA}	40	48	°C/W	
Maximum Junction-to-Case	Steady State	R _{thJC}	0.3	0.36	C/VV	

Notes:

a. Based on T_C = 25 °C. b. Surface mounted on 1" x 1" FR4 board.

c. t = 10 s.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = 250 μA	150			V	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$ 2.5		4.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 120V, V _{GS} = 0 V			1	μА	
		V _{DS} = 120 V, V _{GS} = 0 V, T _J = 55 °C			5		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	157			Α	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		5.2	6.2	mΩ	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 5 V,I _D = 20 A		64		S	
Dynamic ^b							
Input Capacitance	C _{iss}			3200		pF	
Output Capacitance	C _{oss}	$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		765			
Reverse Transfer Capacitance	C _{rss}	1		15			
Total Gate Charge	Qg			43			
Gate-Source Charge	Q _{gs}	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 20 \text{ A}$		15.5		nC	
Gate-Drain Charge	Q _{gd}	1		9			
Gate Resistance	R _g	f = 1 MHz		0.8		Ω	
Turn-On Delay Time	t _{d(on)}			19			
Rise Time	t _r	$V_{DD} = 75 \text{ V, R}_{L} = 3.75 \Omega$		30		- ns	
Turn-Off DelayTime	t _{d(off)}	$I_D \cong 20 \text{ A, V}_{GEN} = 10 \text{ V, R}_g = 6 \Omega$		53			
Fall Time	t _f	1		41			
Drain-Source Body Diode Characterist	ics						
Continous Source-Drain Diode Current	I _S	T _C = 25 °C			157	Α	
Pulse Diode Forward Current (100 μs)	I _{SM}				489		
Body Diode Voltage	V_{SD}	I _S = 1 A			1.2	V	
Body Diode Reverse Recovery Time	t _{rr}	I _F = 15 A, dl/dt = 100 A/µs, T _J = 25 °C		100		ns	
Body Diode Reverse Recovery Charge	Q _{rr}	- 1; - 10 Λ, αι/αι - 100 Λ/μs, 1j - 25 C		150		nC	

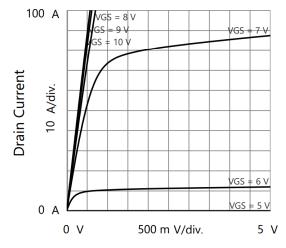
Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

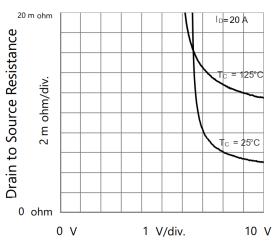
a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$ b. Guaranteed by design, not subject to production testing.



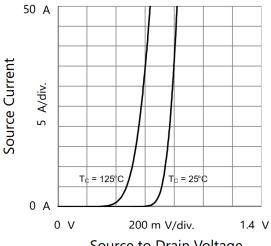
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



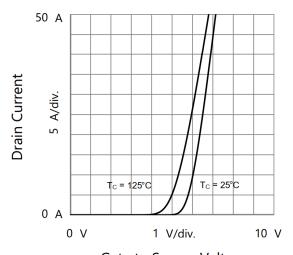
Drain to Source Voltage Output Characteristics



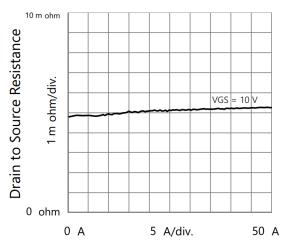
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



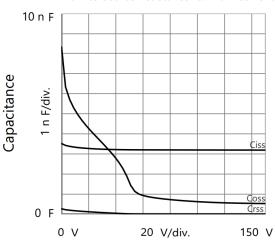
Source to Drain Voltage Body Diode Forward Characteristics



Gate to Source Voltage Transfer Characteristics



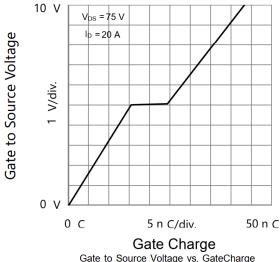
Drain Current
Drain to Source Resistance vs. Drain Current



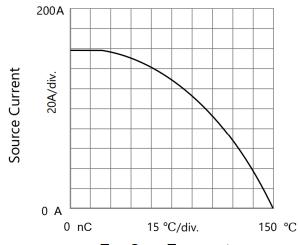
Drain to Source Voltage Capacitances



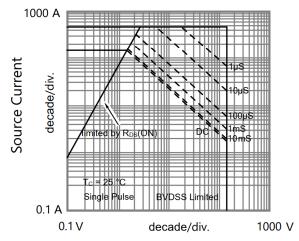
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



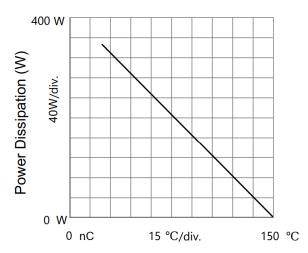
Gate to Source Voltage vs. GateCharge



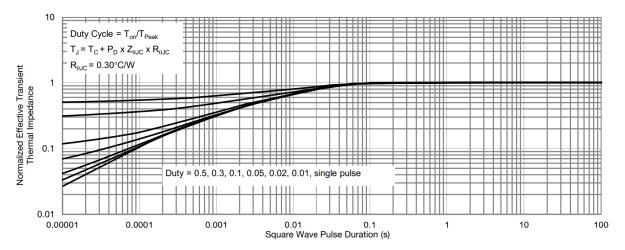
T_C - Case Temperature



Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



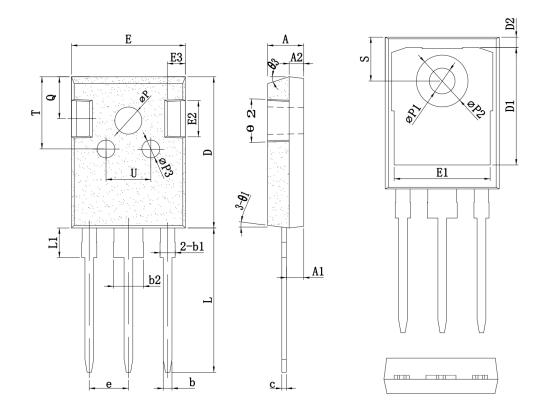
T_C - Case Temperature



Normalized Thermal Transient Impedance, Junction-to-Case



TO-247_3L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
A	4.60	5.00	5.40	e	2.10	5.44	5.70
A1	2.10	2.41	2.70	L	19.00	19.98	21.00
A2	1.70	2.00	2.30	L1	-	-	4.50
b	1.00	1.20	1.40	ФР	3.30	3.70	4.00
b1	1.80	2.10	2.40	ФР1	3.25	3.55	3.85
b2	2.80	3.10	3.40	ФР2	6.80	7.18	7.60
С	0.45	0.60	0.75	ФР3	2.30	2.50	3.30
D	19.00	21.00	23.00	Q	5.50	5.80	6.30
D1	16.00	16.55	17.00	S	5.60	6.15	6.30
D2	0.95	1.20	1.45	T	9.50	10.00	10.50
Е	15.70	15.80	16.50	U	6.00	-	8.00
E1	12.80	13.25	13.70	θ1	5°	7°	9°
E2	4.20	5.00	5.30	θ2	1°	3°	5°
E3	2.20	2.50	2.80	θ3	13°	15°	17°

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